

Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N



PIN Diode Switches Technical Data Sheet

PE71S1103

Features

- Reflective SPDT High Power PIN Diode Switch
- GaN Semiconductor Technology
- Reflective Design
- Frequency Range: 500 MHz to 18 GHz
- Insertion Loss: 1.2 dB typ
- Isolation: 45 dB typ
- VSWR: 1.2:1 typ
- Maximum RF Input Power: +50 dBm
- Input IP3: 55 dBm typ
- Switching Speed: 100 nsec typ
- TTL Compatible Driver Circuitry
- 50 Ohm Design
- N Female Connectors
- Compact Package Design withstands up to 95% Relative Humidity
- -45°C to +85°C Operating Temperature

Applications

- Aerospace & Defense
- Microwave Radio
- Military & Commercial
- Communication
- VSAT
- SATCOM
- Test & Measurement
- Wireless Infrastructure
- Fiber Optics

Description

The PE71S1103 is a high power Reflective SPDT PIN Diode Switch that operates from 500 MHz to 6 GHz. The module utilizes Gallium Nitride (GaN) and chip-and-wire technology in the manufacturing process that ensures state-of-the-art power performance with excellent power-to-volume ratio that's ideal for broadband high power applications. The 50 ohm reflective design has impressive RF input power handling capability for cold switching up to +50 dBm, and incorporates TTL compatible driver circuitry for accurate logic control. Typical performance includes 1.2 dB insertion loss, 45 dB isolation, 1.2:1 VSWR, and 100 nsec switching speed. Operational temperature range is -45°C to +85°C and the bias voltage requirement is +5Vdc. The rugged and compact package supports N female connectors and is designed to meet a series of environmental conditions including Altitude, Vibration, Humidity, and Shock. Model PE71S1108 is the same switch design but includes an integrated heatsink.

Electrical Specifications

TTL Control

 Off/Isolation: 0 to 0.8 V
 On/Low Loss: 2.8 to 5 V

Description	Minimum	Typical	Maximum	Units
Frequency Range	0.5		6	GHz
Impedance		50		Ohms
VSWR		1.2:1	1.6:1	
Insertion Loss		1.2	1.5	dB
IL Temperature Coefficient		0.003		dB/degC
Isolation	35	45		dB
Switching Time		100	250	ns
0.1dB Compression Point			+50	dBm
Input IP3		55		dBm
RF Input Power (CW)*			100	Watts
DC Power Dissipation		0.5		Watt

Click the following link (or enter part number in "SEARCH" on website) to obtain additional part information including price, inventory and certifications: [Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts \(+50 dBm\), 100ns and N PE71S1103](#)

Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N



PIN Diode Switches Technical Data Sheet

PE71S1103

Positive Operating Voltage	5	Vdc
Current @ 5 Vdc	100	mA
Operating Temperature	-45	+85 deg C

Performance by Frequency

Description	F1	F2	F3	F4	F5	Units
Frequency Range	0.5 to 3	3 to 6				GHz
VSWR, Max	1.6:1	1.6:1				
VSWR, Typ	1.4:1	1.4:1				
Insertion Loss, Max	1.3	1.5				dB
Insertion Loss, Typ	1.1	1.3				dB
Isolation, Min	40	35				dB
Isolation, Typ	48	38				dB

Electrical Specification Notes:

Internal TTL Driver will become damaged if Negative Voltage is applied

*Cold Switching: Before changing any TTL signal(s), the RF input power must be blanked or the switch could become damaged

Absolute Maximum Rating

Parameter	Rating
Biassing	+5V±10%
TTL Control Voltage	0~0.8V/2.8~5V



ESD Sensitive Material,
Transport material in
Approved ESD bags.
Handle only in approved
ESD Workstation.

Mechanical Specifications

Size	
Length	1.46 in [37.08 mm]
Width	1.26 in [32 mm]
Height	0.75 in [19.05 mm]
Weight	0.25 lbs [113.4 g]
Design	Reflective, SPDT
RF Connector	N Female

Click the following link (or enter part number in "SEARCH" on website) to obtain additional part information including price, inventory and certifications: [Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts \(+50 dBm\), 100ns and N PE71S1103](#)

Reflective SPDT GaN High Power PIN Diode Switch Operating
from 500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N



PIN Diode Switches Technical Data Sheet

PE71S1103

Environmental Specifications

Temperature

Operating Range
Storage Range

-45 to +85 deg C
-55 to +125 deg C

Humidity

100% RH @ 35°C, 95% RH @ 40°C

Shock

20G for 11ms Half Sinewave, 3 axis both directions

Vibration

25g RMS (15° 2KHz) endurance, 1 hr per axis

Altitude

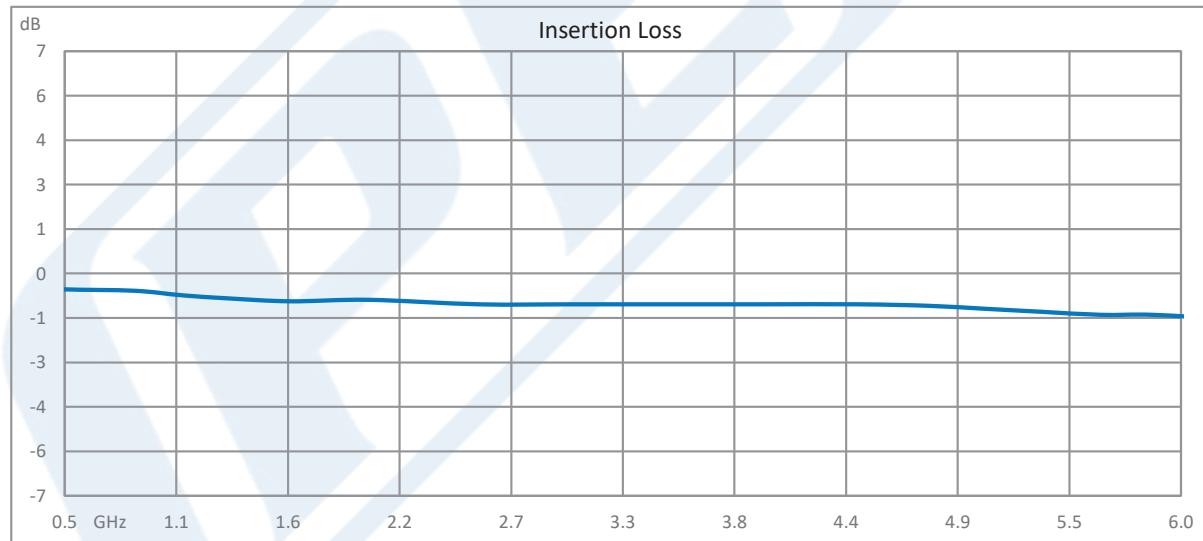
30,000 ft. (Epoxy Sealed Controlled Environment)

Compliance Certifications (see [product page](#) for current document)

Plotted and Other Data

Notes:

Typical Performance Data



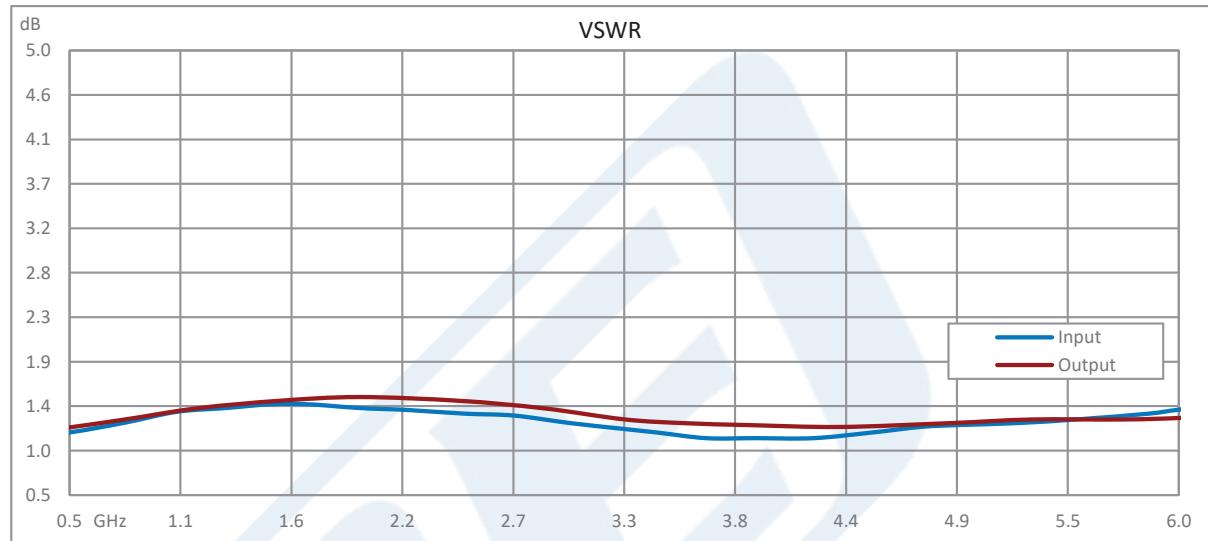
Click the following link (or enter part number in "SEARCH" on website) to obtain additional part information including price, inventory and certifications: [Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts \(+50 dBm\), 100ns and N PE71S1103](#)

Reflective SPDT GaN High Power PIN Diode Switch Operating
from 500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N



PIN Diode Switches Technical Data Sheet

PE71S1103



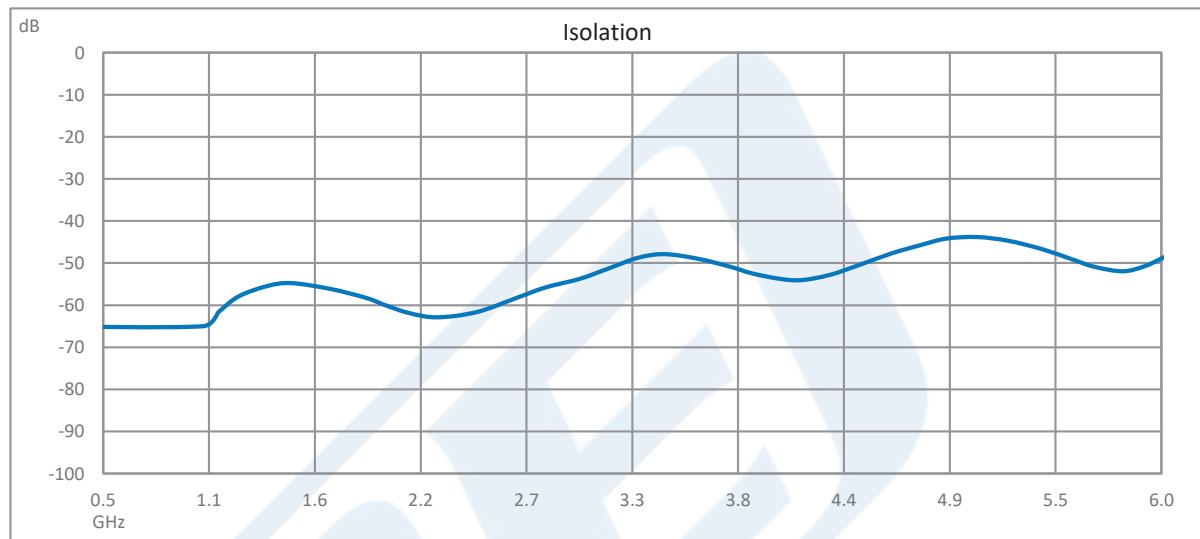
Click the following link (or enter part number in "SEARCH" on website) to obtain additional part information including price, inventory and certifications: [Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts \(+50 dBm\), 100ns and N PE71S1103](#)



Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N

PIN Diode Switches Technical Data Sheet

PE71S1103



Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N from Pasternack Enterprises has same day shipment for domestic and International orders. Our RF, microwave and millimeter wave products maintain a 99.4% availability and are part of the broadest selection in the industry.

Click the following link (or enter part number in "SEARCH" on website) to obtain additional part information including price, inventory and certifications: [Reflective SPDT GaN High Power PIN Diode Switch Operating from 500 MHz to 6 GHz Up to 100 Watts \(+50 dBm\), 100ns and N PE71S1103](#)

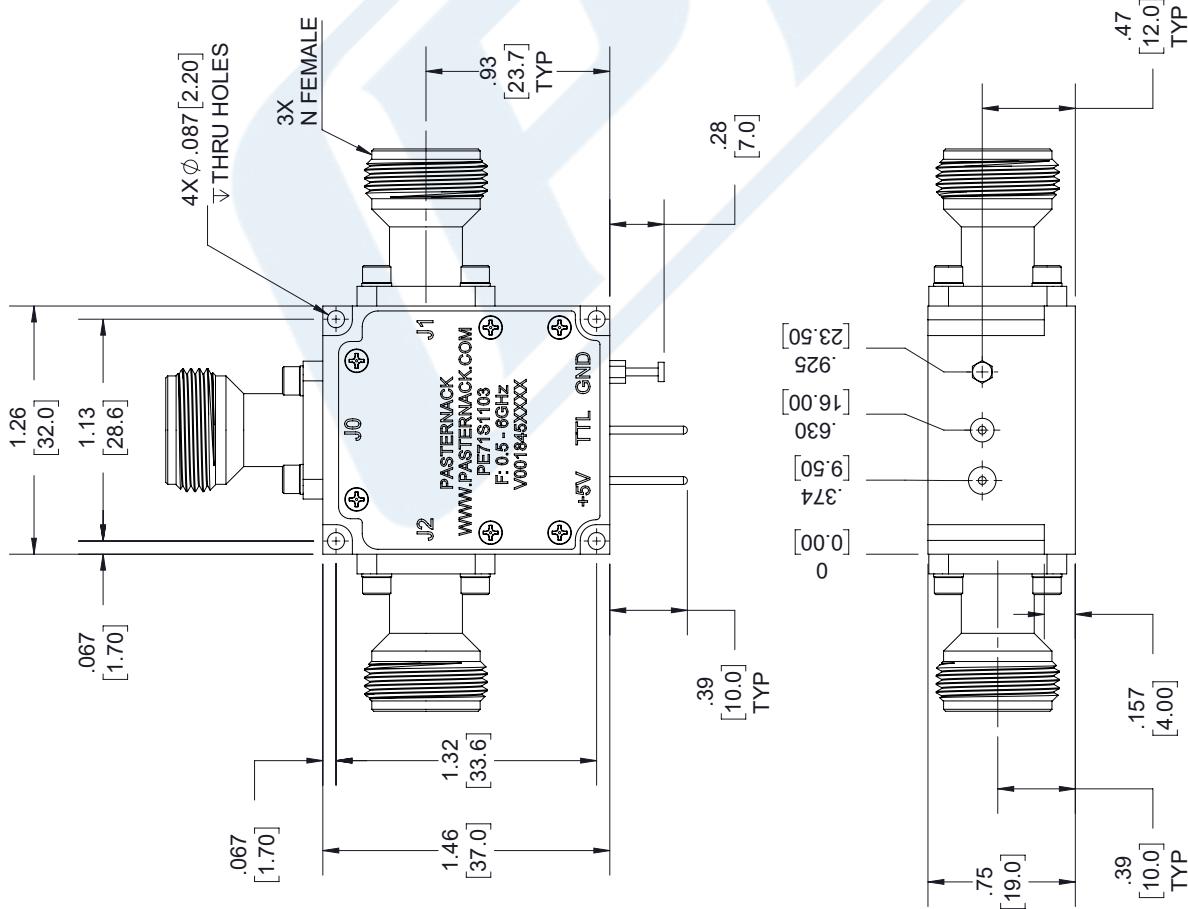
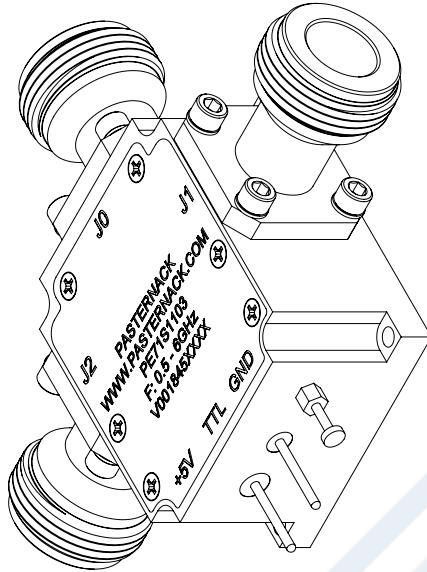
URL: <https://www.pasternack.com/spdt-pin-diode-switch-6-ghz-100-watts-n-pe71s1103-p.aspx>

The information contained in this document is accurate to the best of our knowledge and representative of the part described herein. It may be necessary to make modifications to the part and/or the documentation of the part, in order to implement improvements. Pasternack reserves the right to make such changes as required. Unless otherwise stated, all specifications are nominal. Pasternack does not make any representation or warranty regarding the suitability of the part described herein for any particular purpose, and Pasternack does not assume any liability arising out of the use of any part or documentation.

PE71S1103 CAD Drawing

Reflective SPDT GaN High Power PIN Diode Switch Operating from
500 MHz to 6 GHz Up to 100 Watts (+50 dBm), 100ns and N

REVIEWS			
REV.	DESCRIPTION	DATE	APPROVED
A	INITIAL RELEASE	7/16/2020	T.GALLA



Truth Table			
Control Input TTL	Signal Path State	J0-J1	J0-J2
1		0	
0			0

 PASTERNACK an INFINITE brand	THE INFORMATION AND DESIGN IN THIS DOCUMENT IS THE PROPERTY OF PASTERNACK CORPORATION. ALL RIGHTS RESERVED.	THIRD ANGLE PROJECTION
Pasterнак Enterprises, Inc. P.O. Box 16759, Irvine, CA 92623. Phone: 1.949.261.1920 1.866.727.8376 Fax: 1.949.261.7451 Website: www.pasterнак.com E-mail: sales@pasterнак.com	1	1
SIZE CAGE CODE DRAWN BY A 53919 K.DANG	ITEM NO. REV	PE71S1103 A

UNLESS OTHERWISE SPECIFIED
LEADING DIMENSIONS ARE INCHES
DIMENSIONS IN [] ARE MILLIMETERS
TOLERANCES:

FRACTIONS
X = ± 2 [5.08] ± 1/32
XX = ± .02 [5.51] .005 [1.31]
XXX = ± .005 [1.31] ANGLES ± 1°
CABLE LENGTH (L) TOLERANCES:
L ≤ 12 [305] = +1 [25] / -0
12 [305] < L ≤ 60 [1524] = +2 [51] / -0
60 [1524] < L ≤ 120 [3048] = +4 [102] / -0
120 [3048] < L ≤ 300 [7620] = +6 [152] / -0
300 [7620] < L = +5% L / -0

THESE COMMODITIES, TECHNOLOGY OR SOFTWARE WERE EXPORTED FROM THE UNITED STATES IN ACCORDANCE
WITH THE EXPORT ADMINISTRATION REGULATIONS. DIVERSION CONTRARY TO U.S. LAW PROHIBITED.